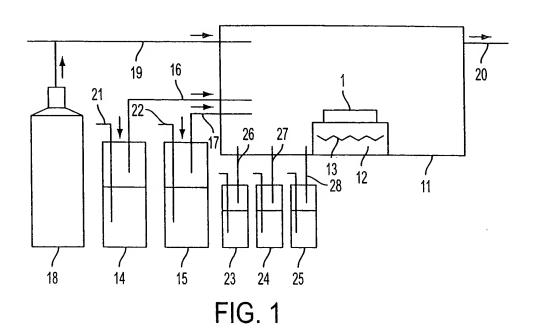


Rule 53(b) Continuation Appln. of Appln. No. 09/473,70 Inventor(s): Hideki HAYASHIDA, et al. Appln. No.: To Be Assigned; Filed: April 12, 2004 For: 'Ammonia For Use In Manufacture of GAN-Type Compound Semiconductor And Method For Manufacturing GAN-Type Compound Semiconductor SUGHRUE Tel. No. 202-293-7060; Ref. No. Q81061 I of 2





Rul* 53(b) Continuation Appln. of Appln. No. 09/473,708 In. (s): Hideki HAYASHIDA, et al. Al., No.: To Be Assigned; Filed: April 12, 2004 For: Ammonia For Use In Manufacture of GAN-Type Compound Semiconductor And Method For Manufacturing GAN-Type Compound Semiconductor SUGHRUE Tel. No. 202-293-7060; Ref. No. Q81061 2 of 2

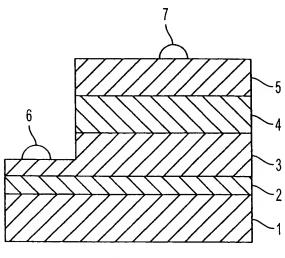


FIG. 3

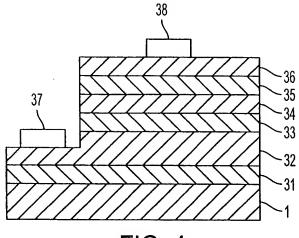


FIG. 4



Replacement Sheet U.S. Application No.: 10/821,944 Inventor: Hideki HAYASHIDA et al. Group Art Unit: 2818 / Conf. No. 2372 Sheet 1 of 1

